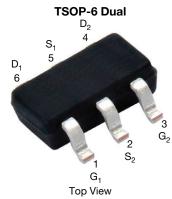
SQ3987EV

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Vishay Siliconix

Automotive Dual P-Channel 30 V (D-S) 175 °C MOSFET



Marking code: 8X

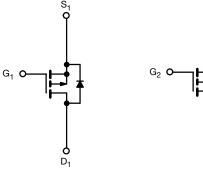
PRODUCT SUMMARY					
V _{DS} (V)	-30				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -10 V$	-0.110				
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	-0.185				
I _D (A)	-2.75				
Configuration	Dual				
Package	TSOP-6				

FEATURES

- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_g and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

D₂ P-Channel MOSFET

S,

ABSOLUTE MAXIMUM RATINGS	Γ _A = 25 °C, unless α	otherwise noted)		
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	V _{DS}	-30	V	
Gate-source voltage	V _{GS}	± 20	v	
Continuous drain current (T _J = 150 °C) ^a	T _C = 25 °C		-3	
	T _C = 125 °C	I _D	-1.74	A
Pulsed drain current	I _{DM}	-11	A	
Continuous source current (diode conduction) ^a	I _S	-2.1		
Maximum power dissipation ^a	T _C = 25 °C	D	1.67	w
	T _C = 125 °C	P _D	0.56	V
Unclamped inductive surge UIS	·	I _{AV}	-5	A
Operating junction and storage temperature range	je	T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Maximum junction-to-ambient ^a	Steady state	R _{thJA}	150	°C/W		
Maximum junction-to-foot (drain)	Steady state	R _{thJF}	90	0/10		

Note

a. Surface mounted on 1" x 1" FR4 board

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SPECIFICATIONS (T _J	= 25°C, ur	less otherwise	noted)				
PARAMETER	SYMBOL	T	MIN.	TYP.	MAX.	UNIT	
Static				•	•	•	
Gate threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.5	-	-2.5	V
Gate-body leakage	I _{GSS}	V _{DS}	$_{\rm S} = 0$ V, V _{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain		$V_{GS} = 0 V$	V _{DS} = -30 V	-	-	-1	μA
current	IDSS	$V_{GS} = 0 V$	V _{DS} = -30 V, T _J = 175 °C	-	-	-50	
On-state drain current a	I _{D(on)}	V _{GS} = -10 V	$V_{DS} \le -5 V$	-4	-	-	Α
Drain-source on-state	D	$V_{GS} = -10 V$	I _D = -1.5 A	-	0.085	0.133	
resistance ^a	R _{DS(on)}	V _{GS} = -4.5 V	I _D = -2 A	-	0.135	0.185	Ω
Forward transconductance a	g _{fs}	V	_{DS} = -5 V, I _D = -1 A	-	4.2	-	S
Diode forward voltage ^a	V _{SD}	I _S	= -0.5 A, V _{GS} = 0 V	-	-0.83	-1.10	V
Dynamic ^b							
Input capacitance	Ciss			-	456	570	
Output capacitance	Coss	$V_{GS} = 0 V$	V _{DS} = -15 V	-	85	106	pF
Reverse capacitance	C _{rss}			-	59	74	
Total gate charge	Qg	V _{GS} = -10 V	V _{DS} = -15 V, I _D = -3 A	-	9.7	12.2	nC
Gate-source charge	Q _{gs}			-	1.3	-	
Gate-drain charge	Q _{qd}			-	2	-	1
Gate resistance	R _g		f = 1 MHz		-	24	Ω
Turn-on delay time	t _{d(on)}	V_{DD} = -10 V, R _L = 10 Ω, $I_D \cong$ -1 A, V _{GEN} = -10 V, R _g = 1 Ω		-	6.6	8.3	- ns
Rise time	t _r			-	2.4	3	
Turn-off delay time	t _{d(off)}			-	18.4	23	
Fall time	t _f			-	2.2	2.8	
Source-Drain Diode Ratings	and Charac	teristic ^b					
Pulsed current	I _{SM}			-	-	-11	Α
Forward voltage	V _{SD}	$I_{\rm F} = 0.5 \text{ A}, V_{\rm GS} = 0 \text{ V}$		-	-0.83	-1.1	V
Reverse recovery fall time	t _a	V _{DD} = -24 V, I _{FM} = -1.5 A, di/dt = 100 A/μs, R = 160 Ω, L = 1 mH, pulse W = 2 μs		-	9.1	-	ns
Reverse recovery rise time	t _b			-	4.8	-	ns
Body diode reverse recovery time	t _{rr}			-	14	28	ns
Body diode reverse recovery charge	Q _{rr}			-	9	18	μC
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.4	-	А

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

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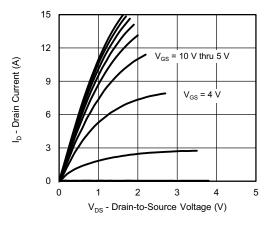
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

2

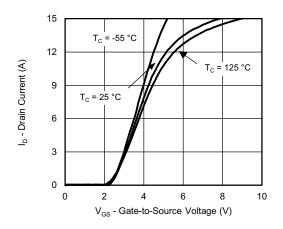


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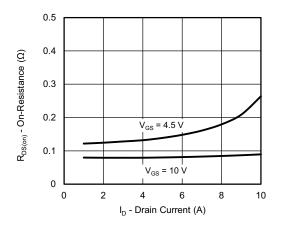
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



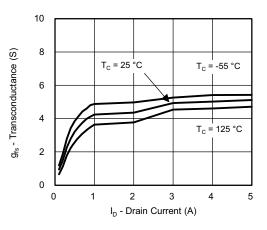
Output Characteristics



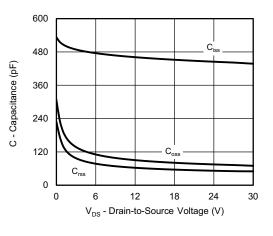
Transfer Characteristics



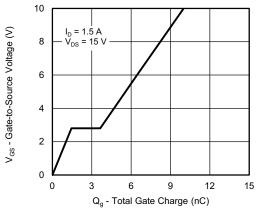
On-Resistance vs. Drain Current



Transconductance



Capacitance



Gate Charge

S19-0398-Rev. B, 06-May-2019

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Document Number: 75315

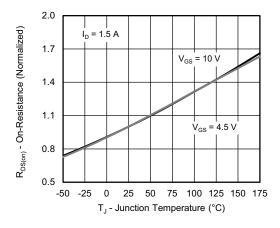
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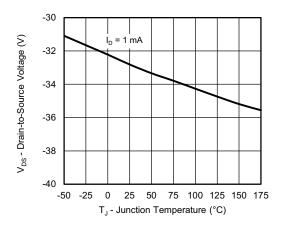
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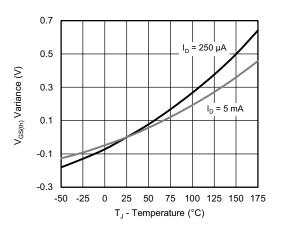
TYPICAL CHARACTERISTICS (25 °C unless otherwise noted)



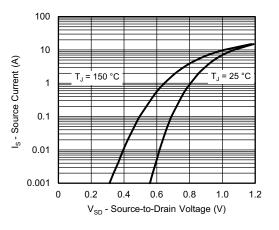
On-Resistance vs. Junction Temperature



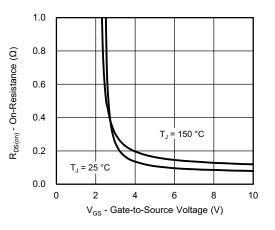
Drain Source Breakdown vs. Junction Temperature



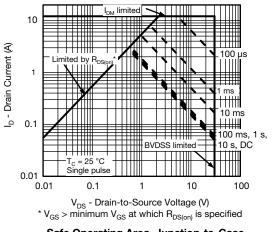
Threshold Voltage



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



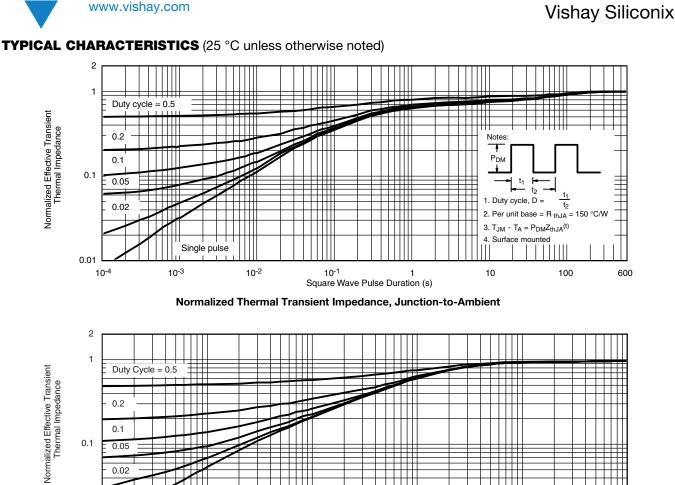
Safe Operating Area, Junction-to-Case

S19-0398-Rev. B, 06-May-2019

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10-2

Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Foot

10-1

/ISHAY

0.02

0.01

10-4

Single Pulse

10⁻³

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SQ3987EV

1

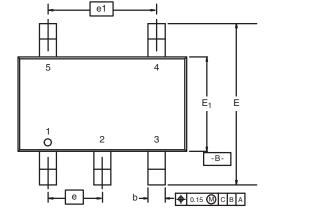
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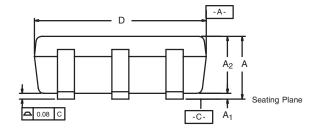
Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C

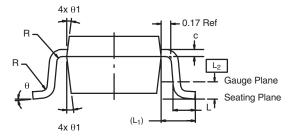








6-LEAD TSOP



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁	0.60 Ref			0.024 Ref			
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Application Note 826

Vishay Siliconix



RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)

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